



FSS248 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Motor drive applications.
- Inverter drive applications.
- 4V drive.

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		45	V
Gate-to-Source Voltage	V_{GSS}		± 20	V
Drain Current (DC)	I_D		7	A
Drain Current ($PW \leq 10\text{s}$)	I_D	Duty cycle $\leq 1\%$	7.5	A
Drain Current ($PW \leq 10\mu\text{s}$)	I_{DP}	Duty cycle $\leq 1\%$	28	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (1200mm \times 0.8mm), $PW \leq 10\text{s}$	1.8	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1\text{mA}$, $V_{GS}=0\text{V}$	45			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=45\text{V}$, $V_{GS}=0\text{V}$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16\text{V}$, $V_{DS}=0\text{V}$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}$, $I_D=1\text{mA}$	1.2		2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10\text{V}$, $I_D=7\text{A}$	4.1	6.9		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=7\text{A}$, $V_{GS}=10\text{V}$		23	30	$\text{m}\Omega$
	$R_{DS(on)2}$	$I_D=3.5\text{A}$, $V_{GS}=4\text{V}$		39	55	$\text{m}\Omega$

Marking : S248

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FSS248

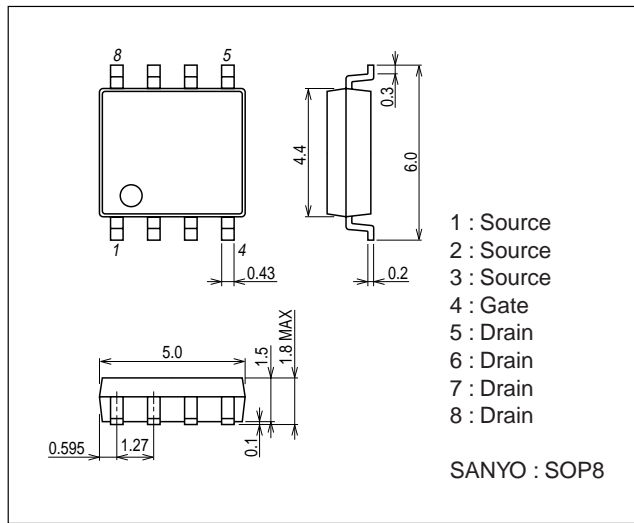
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	$V_{DS}=20V, f=1MHz$		1040		pF
Output Capacitance	Coss	$V_{DS}=20V, f=1MHz$		145		pF
Reverse Transfer Capacitance	Crss	$V_{DS}=20V, f=1MHz$		105		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		14		ns
Rise Time	t_r	See specified Test Circuit.		90		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		85		ns
Fall Time	t_f	See specified Test Circuit.		75		ns
Total Gate Charge	Qg	$V_{DS}=24V, V_{GS}=10V, I_D=7A$		23		nC
Gate-to-Source Charge	Qgs	$V_{DS}=24V, V_{GS}=10V, I_D=7A$		3.5		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=24V, V_{GS}=10V, I_D=7A$		5		nC
Diode Forward Voltage	VSD	$I_S=7A, V_{GS}=0V$		0.81	1.2	V

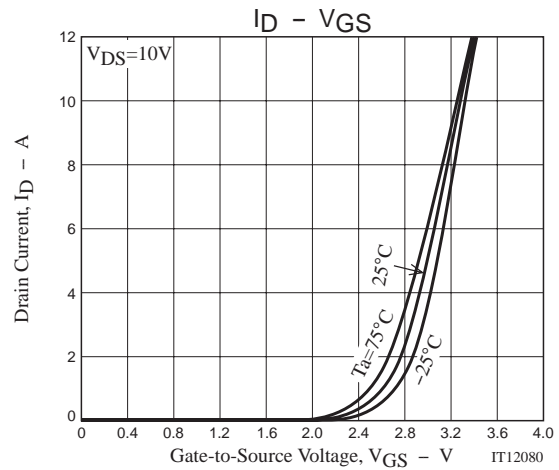
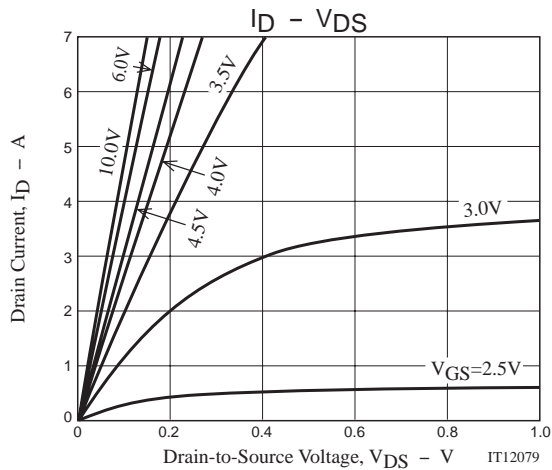
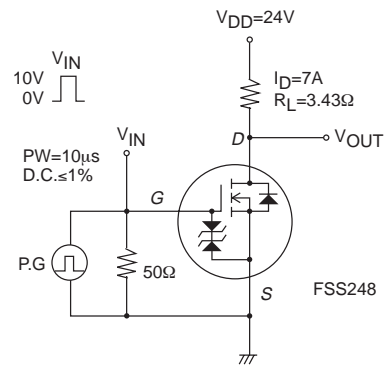
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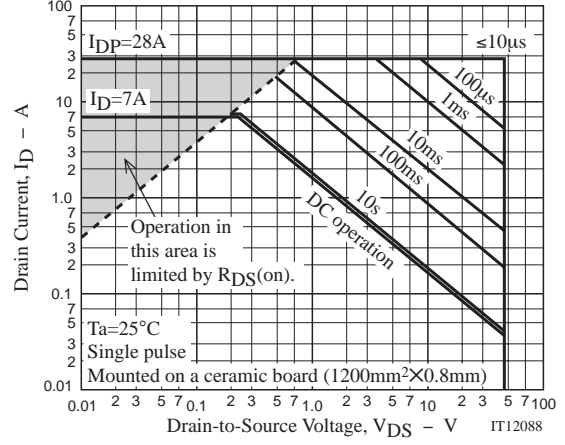
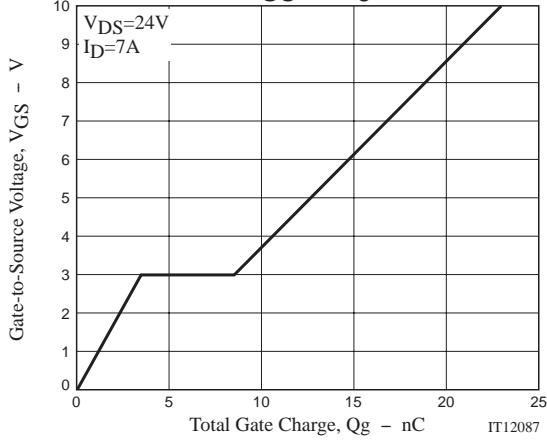
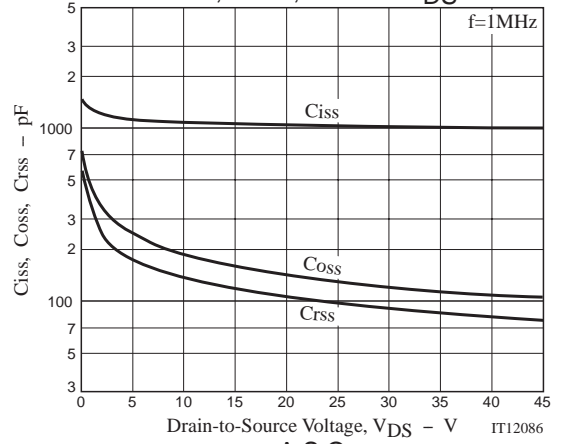
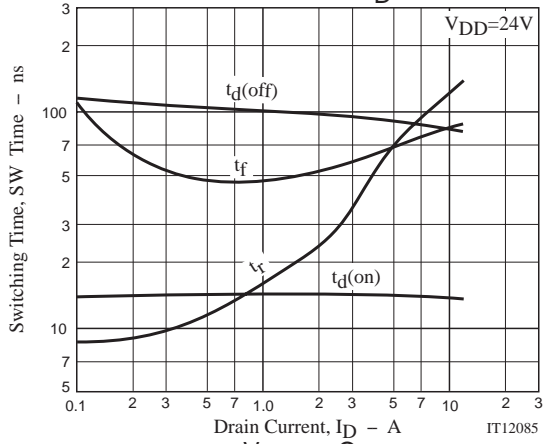
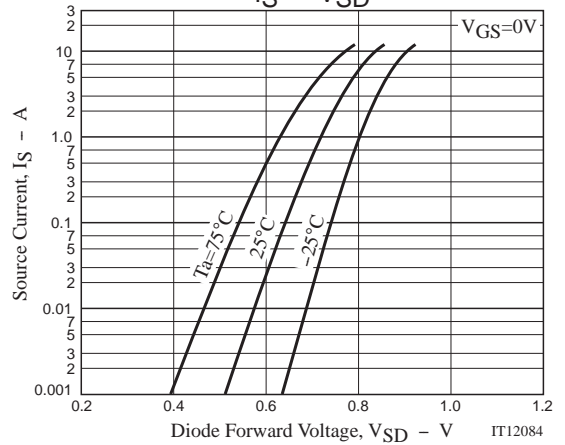
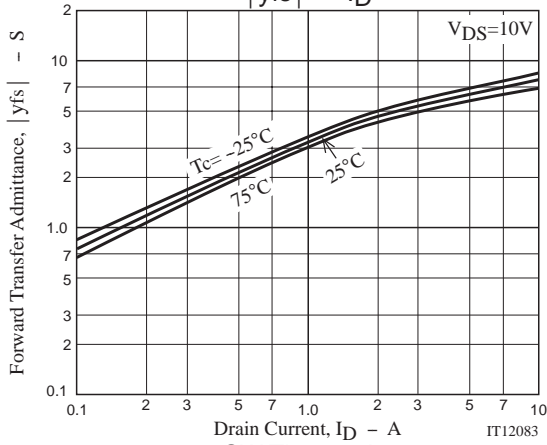
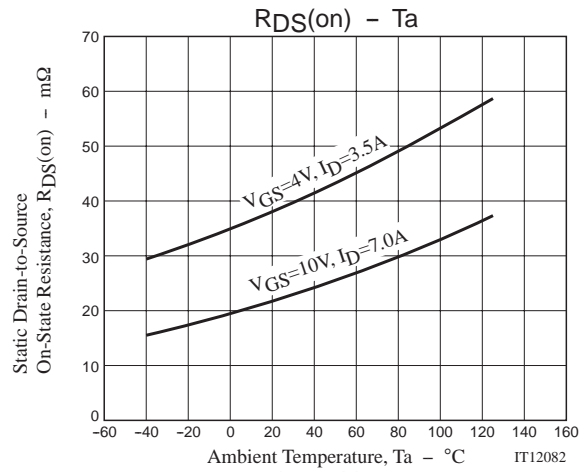
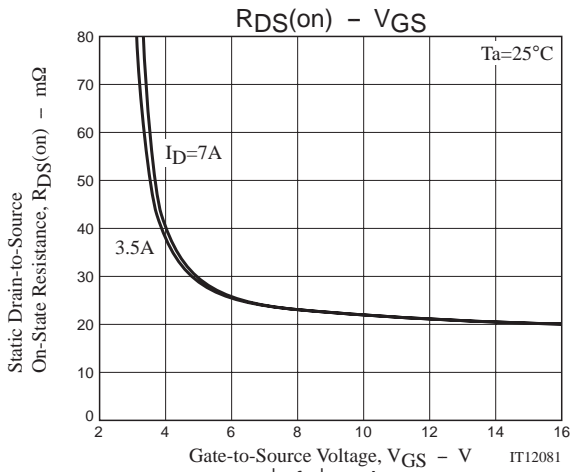
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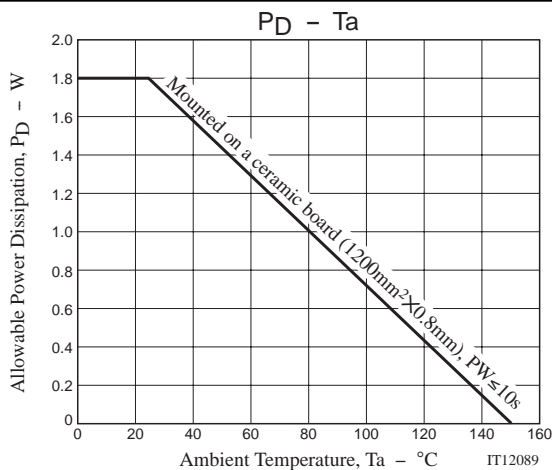
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Switching Time Test Circuit







Note on usage : Since the FSS248 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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